	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Errors
1	BRS	L1	4507	(oxide or "silicon oxide" or "silicon dioxide") same (lpcvd or "low pressure chemical vapor deposition") same temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:35			
2	BRS	L2	2482	((oxide or "silicon oxide" or "silicon dioxide") with (lpcvd or "low pressure chemical vapor deposition")) same temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:37			
3	BRS	L3	1755	2 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:38			
4	BRS	L4		((oxide or "silicon oxide" or "silicon dioxide") with (lpcvd or "low pressure chemical vapor deposition")) same temperature same (known or conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:41			
5	BRS	L5	497	4 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:42			
6	BRS	L6	668	((oxide or "silicon oxide" or "silicon dioxide" or MTO or "mid temperature oxide") with (lpcvd or "low pressure chemical vapor deposition")) same temperature same (known or conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:58			
7	BRS	L7	497	6 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:47			
8	BRS	L8	575	(temperature with ".degree. C." or "C")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 09:47			

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Errors
9	BRS	L9	460	8 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 10:00			
10	BRS	L10	3	(((oxide or "silicon oxide" or "silicon dioxide" or MTO or "mid temperature oxide") with buffer) with (lpcvd or "low pressure chemical vapor deposition")) same temperature same (known or conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 11:45			
11	BRS	L11		((MTO or "mid temperature oxide") with (lpcvd or "low pressure chemical vapor deposition")) same temperature same (known or conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 10:02			
12	BRS	L12	2	11 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 10:03			
13	BRS	L13	6	((MTO or "mid temperature oxide" or "middle temperature oxide") with (lpcvd or "low pressure chemical vapor deposition")) same temperature same (known or conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 10:02			*
14	BRS	L14	2	13 and @pd<="20031114"		2006/08 /31 10:05			
15	BRS	L15	8	((buffer) with (lpcvd or "low pressure chemical vapor deposition")) same temperature same (known or conventional)		2006/08 /31 10:05			
16	BRS	L16	6	15 and @pd<="20031114"	11.51 11.14	2006/08 /31 11:20			

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Definition	Errors
17	BRS	L17	5078	((etch\$3 with (phosphoric or H3PO4 or "H.sub.3PO.sub.4"))) same (nitride or SiN or Si3N4 or "Si.sub.3N.sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 11:16			
18	BRS	L19	10	18 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 11:21			
19	BRS	L20	3	(("silicon oxide" or "silicon dioxide") with (hdcvd or "high density chemical vapor deposition") with (form\$3 or formation))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 12:22			
20	BRS	L21	7	CHO-YONG-JOON.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 12:22			
21	BRS	L22	47	KIM-YOUNG-HEE.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/08 /31 12:23			
22	BRS	L23	22	YUN-YOUNG-HWAN.in.	EPO: IPO:	2006/08 /31 12:24			
23	BRS	L24	4	BAEK-DOO-HEUN.in.	HISLA R	2006/08 /31 12:24			